SEMICONDUCTOR DEVICE AND METHOD OF FORMATION

Abstract of the Disclosure

An interconnect (128) overlies a semiconductor device substrate (100). In one embodiment, a conductive barrier layer (82) overlies a portion of the interconnect (128), a passivation layer (92) overlies the conductive barrier layer (82) and the passivation layer (92) has an opening that exposes portions of the conductive barrier layer (82). In an alternate embodiment a passivation layer (22) overlies the interconnect, the passivation layer (22) has an opening (24) that exposes the interconnect (128) and a conductive barrier layer (32) overlies the interconnect (128) within the opening (24).

(Fig. 4 and 12 to accompany abstract)